



30V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BVDSS	R _{DS(ON)} Max	I _D Max T _A = +25°C
001/	15mΩ @ V _{GS} = 10V	9.3A
30V	20mΩ @ V _{GS} = 4.5V	8.1A

Features

- 0.6mm Profile Ideal for Low Profile Applications
- PCB Footprint of 4mm²
- Low Gate Threshold Voltage
- · Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

Description

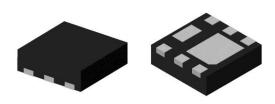
This MOSFET is designed to minimize the on-state resistance (RDS(ON)), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Battery Management Application
- Power Management Functions
- DC-DC Converters

Mechanical Data

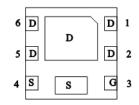
- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (e4)
- Weight: 0.007 grams (Approximate)

U-DFN2020-6 (Type F)

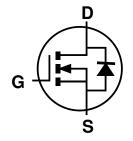


Top View

Bottom View



Pin Out Bottom View



Internal Schematic

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN3021LFDF-7	U-DFN2020-6 (Type F)	3,000/Tape & Reel
DMN3021LFDF-13	U-DFN2020-6 (Type F)	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



Marking Information

Site 1



F2 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: H = 2020) M = Month (ex: 9 = September)

Date Code Key

2410 0000 110)												
Year	2015		2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	С		Н		J	K	L	М	N	0	Р	R
								A	Com	0-4	Nav	D
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec

Site 2



F2 = Product Type Marking Code YWX = Date Code Marking

Y = Year (ex: 0 = 2020)
W = Week (ex: a = Week 27; z Represents Week 52 and 53)
X = Internal Code (ex: U = Monday)

Date Code Key

Year	2015	 2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	5	 0	1	2	3	4	5	6	7	8	9

Week	1-26	27-52	53
Code	A-Z	a-z	Z

Internal Code	Sun	Mon	Tue	Wed	Thu	Fri	Sat
Code	T	U	V	W	Χ	Υ	Z



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage			V_{DSS}	30	V
Gate-Source Voltage			Vgss	±20	V
Continuous Drain Current (Note C) Voc. 10V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	ΙD	9.3 7.5	Α
Continuous Drain Current (Note 6) V _{GS} = 10V	t<5s	$T_A = +25$ °C $T_A = +70$ °C	D	11.8 9.4	Α
Pulsed Drain Current (380µs Pulse, Duty Cycle = 1%	6)		I _{DM}	50	Α
Maximum Continuous Drain-Source Diode Forward (Is	1.8	Α		
Avalanche Current (Note 7) L = 0.1mH	I _{AS}	18	Α		
Avalanche Energy (Note 7) L = 0.1mH			Eas	16	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	$T_A = +25^{\circ}C$	Pn	0.73	W
Total Fower Dissipation (Note 3)	$T_A = +70$ °C	PD	0.47	VV
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	Roja	174	°C/W
Thermal nesistance, sunction to Ambient (Note 3)	t < 5s	МӨЈА	112	C/VV
Total Power Dissipation (Note 6)	$T_A = +25^{\circ}C$	D-	2.03	W
Total Fower Dissipation (Note o)	$T_A = +70$ °C	PD	1.30	
Thermal Pegistenes, Jungtion to Ambient (Note 6)	Steady State	Davi	64	
Thermal Resistance, Junction to Ambient (Note 6)	t < 5s	Roja	40	°C/W
Thermal Resistance, Junction to Case (Note 6)	Steady State	Rejc	13	
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)					L	•
Drain-Source Breakdown Voltage	BV _{DSS}	30	_	_	V	$V_{GS} = 0V, I_{D} = 250\mu A$
Zero Gate Voltage Drain Current T _J = +25°C	IDSS	_	_	1	μΑ	V _{DS} = 30V, V _{GS} = 0V
Gate-Source Leakage	lgss	_	_	±100	nA	$V_{GS} = \pm 20V$, $V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)		•		•		·
Gate Threshold Voltage	V _{GS(TH)}	1.0	1	2.2	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$
Static Drain-Source On-Resistance	D		_	15	mΩ	$V_{GS} = 10V, I_{D} = 7A$
Static Drain-Source On-Nesistance	R _{DS(ON)}		-	20	11177	$V_{GS} = 4.5V$, $I_D = 7A$
Diode Forward Voltage	V _{SD}	_	0.8	1.2	V	V _G S = 0V, I _S = 2.2A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	Ciss		706			V 45V V 0V
Output Capacitance	Coss	_	112	_	pF	$V_{DS} = 15V, V_{GS} = 0V,$ f = 1.0MHz
Reverse Transfer Capacitance	Crss	_	81	_		1 = 1.001112
Gate Resistance	R _G	_	2.6	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$
Total Gate Charge (VGS = 10V)	Qg	_	14	_		
Total Gate Charge (VGS = 4.5V)	QG	_	6.7	_	nC	\
Gate-Source Charge	Q _{GS}	_	1.9	_	nc nc	$V_{DS} = 15V, I_{D} = 5A$
Gate-Drain Charge	Q _{GD}	_	2.5	_		
Turn-On Delay Time	td(ON)	_	5.4	_		
Turn-On Rise Time	tR	_	6.8	_		$V_{DS} = 15V, V_{GS} = 4.5V,$
Turn-Off Delay Time	tD(OFF)	_	9.7	_	ns	$R_g = 1.7\Omega$, $I_D = 5A$
Turn-Off Fall Time	t _F	_	4.7	_		

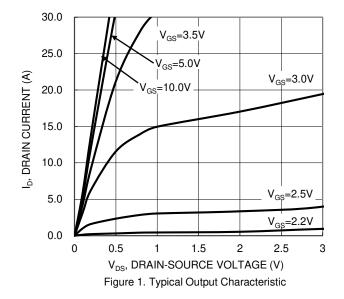
5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout. 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate. Notes:

^{7.} I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep $T_{J} = +25^{\circ}C$.

^{8.} Short duration pulse test used to minimize self-heating effect.

^{9.} Guaranteed by design. Not subject to product testing.





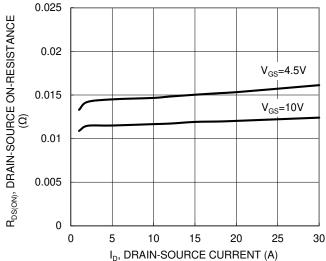


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

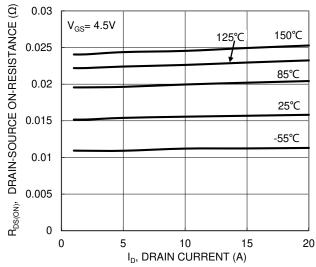


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

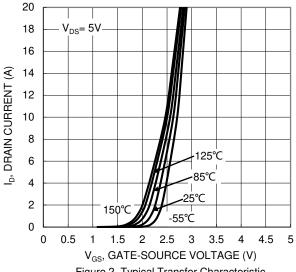


Figure 2. Typical Transfer Characteristic

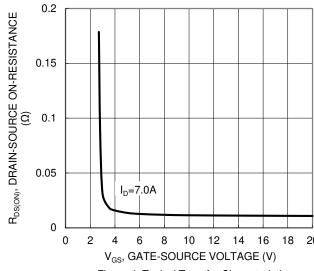


Figure 4. Typical Transfer Characteristic

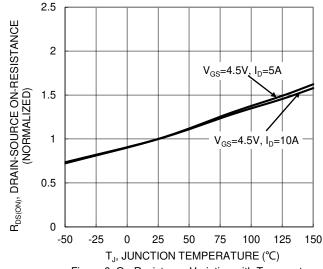


Figure 6. On-Resistance Variation with Temperature



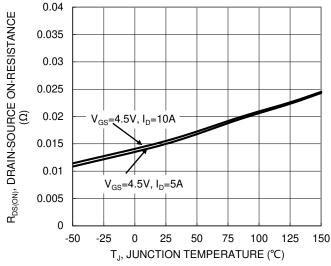
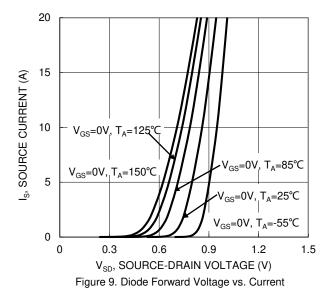
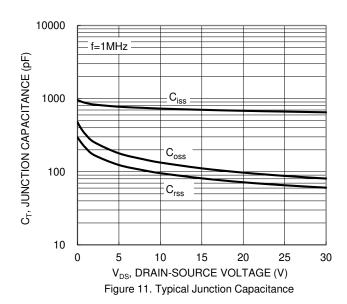


Figure 7. On-Resistance Variation with Temperature





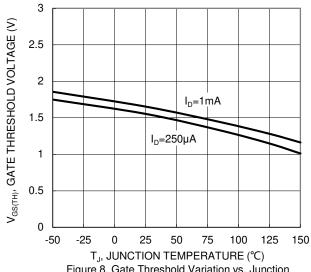


Figure 8. Gate Threshold Variation vs. Junction Temperature

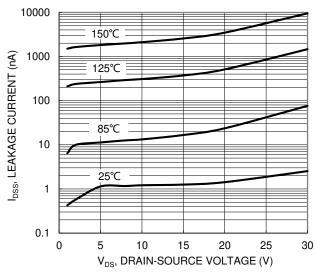


Figure 10. Typical Drain-Source Leakage Current vs. Voltage

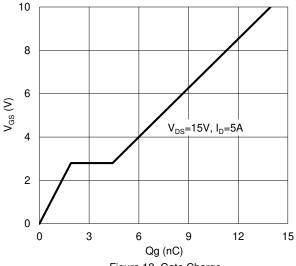
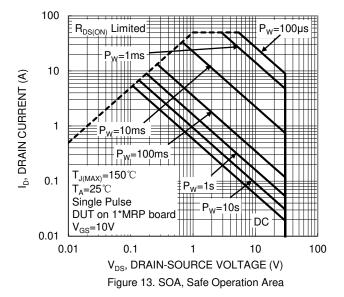


Figure 12. Gate Charge





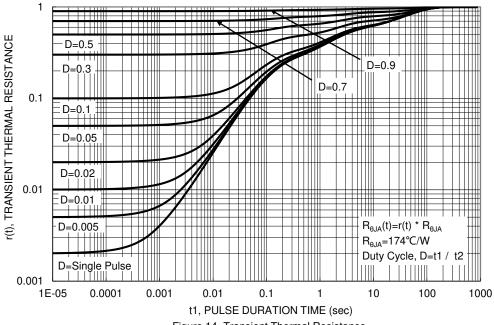


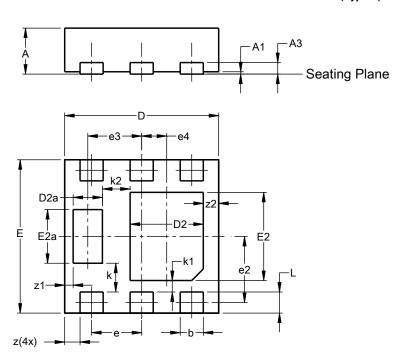
Figure 14. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type F)

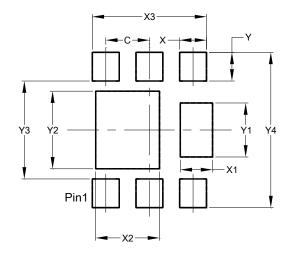


U-DFN2020-6								
(Type F)								
Dim	Min	- 71						
Α	0.57	0.63	0.60					
A1	0.00	0.05	0.03					
A3	-	-	0.15					
b	0.25	0.35	0.30					
D	1.95	2.05	2.00					
D2	0.85	1.05	0.95					
D2a	0.33	0.43	0.38					
Е	1.95	2.05	2.00					
E2	1.05	1.25	1.15					
E2a	0.65	0.75	0.70					
е		0.65 BS	С					
e2).863 BS						
е3		0.70 BS	С					
e4	().325 BS	SC					
k		0.37 BS	С					
k1		0.15 BS						
k2		0.36 BS						
L	0.225 0.325 0.275							
Z	0.20 BSC							
z1	().110 BS	SC					
z2		0.20 BS	С					
All C	Dimens	ions in	mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type F)



Dimensions	Value
בוווכווסוטווס	(in mm)
С	0.650
X	0.400
X1	0.480
X2	0.950
Х3	1.700
Y	0.425
Y1	0.800
Y2	1.150
Y3	1.450
Y4	2.300



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